

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電 気 的 特 性 ($T_c=25^\circ\text{C}$)										外 形	備 考				
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス I_{cE}		バイアス		h_{FE}	h_{ie}	h_{re}	h_{oe}	$f_{\alpha b}$			C_{ob}	$r_{bb'}$		
				5					6		7		8				9		10		11		12	

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cB0} MAXIMUM VALUE AND V_{cB} VALUE (CRITERIA FOR MEASURING I_{cB0})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{cE} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{cB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考		
				V _{CE0} (V)	V _{BE0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CEB} (V)	直流又はバリス h _{FE}		バイアス		h _{fe} h _{fb} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μΩ)	f _{αB} f _T * (Mc)			C _{ob} (pF)	r _{bb} ' h _{ie} (real)* (Ω)
											V _{CE} (V)	I _C (mA)	V _{CEB} (V)	I _E (mA)									
★ 2SC1931	富士通	Diff	Si.EP	16	3	30	150/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	3 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (3V, 10mA)	8000*	0.45	50*	263				
★ "	"	"	"	16	3	30	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	3 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (3V, 10mA)	8000*	0.45	50*	264A				
"	"	"	"	15	3	40	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	3 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (3V, 20mA)	6000*	0.65	50*	263				
"	"	"	"	20	3	80	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	3 10	6	-30	ΔV _{BE} < 30mV, γΔV _{BE} < 60μV/°C (5V, 30mA)	6000*	0.9	50*	285				
★ "	"	RF	"	15	3	30	250	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	6 10	6	-20		6000*	0.4	25*	284				
★ "	"	Diff	"	15	3	30	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	6 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (6V, 10mA)	6000*	0.6	50*	263				
★ "	"	RF	"	15	3	70	300	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	6 40	6	-40		6000*	0.7	20*	284				
★ "	"	Diff	"	15	3	30	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	6 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (6V, 10mA)	6000*	0.6	50*	264B				
★ "	"	"	"	15	3	30	200/unit	175	0.1	10	80 h _{FE1} /h _{FE2} = 0.6-1.0	6 10	6	-20	ΔV _{BE} < 20mV, γΔV _{BE} < 60μV/°C (6V, 20mA)	6000*	0.6	50*	264A				
"	日電	PA	Si.E	120	5	50	1W	150	0.1	120	200	10	10	-10		120*	2.3		278 2SA915 とコンプリ)				
"	"	"	"	160	5	50	1W	150	0.1	160	200	10	10	-10		120*	2.3		278 2SA916 とコンプリ)				
"	日立	SW	Si.T	1500	6	3A	50W (T _c =25°C)	150	10	600				5	-200	t _J < 1μS	5*	90	15	102 水平偏向用			
"	三菱	PA	Si.EP	35	4	400	3W (T _c =25°C)	175	100	15	50	10	100		P ₀ = 0.4W (f = 470MHz, V _{CE} = 13.5V, P _i = 30mW)				255				
"	1944																						
"	三菱	PA	Si.EP	80	5	6A	20W (T _c =25°C)	150	100	30	50	10	100		P ₀ = 16W, η = 70% (f = 27MHz, V _{CE} = 12V, P _i = 0.5W)				301A				
"	1946	"	"	35	4	7A	50W (T _c =25°C)	175	2mA	25	50	10	200		P ₀ = 32W, η = 70% (f = 175MHz, V _{CE} = 13.5V, P _i = 6W)				272				
"	1947	"	"	35	4	1A	10W (T _c =25°C)	175	500	25	50	10	100		P ₀ = 4W, η = 60% (f = 175MHz, V _{CE} = 13.5V, P _i = 0.3W)				84B				
"	日電	RF.LN	Si.E	15	3	20	150	200	1	8	80	8	10	8	-10	G _{re} = 8.5dB (8V, 10mA, 4GHz)	8000*	C _{re} 0.3		339			
"	1949	"	"	30	3	130	580	200	0.1	20	100	5	50	5	-50	S _{21c} ² = 9.2dB (5V, 50mA, 1GHz)	2700*	C _{re} 1		306			
"	1950	"	RF.PA	28	3	200	5W (T _c =25°C)	200	0.5	10	40	6	100	6	-100	S _{21c} ² = 4dB (f = 1GHz, V _{CE} = 6V, I _C = 100mA)	4000*	C _{re} 1.5	25*	311			
"	ソニー	RF	"	120	5	100	750	120	0.2	100	150	5	3	10	-20	A _{re} = 8dB (f = 100MHz)		2.4	C _e = 45pS	259 2SA917 とコンプリ)			
"	日電	RF.LN	"	45	3	300	800	200	0.1	20	80	10	50	15	-50	G _{re} = 18dB (15V, 50mA, 200MHz)	2000*	2		84B			
"	1953	松下	AF.PA	150	5	100	1W	150	1	100	65-450	5	10	10	-10		200*			222 2SA914 とコンプリ)			
"	1954	富士通	RF	25	3	150	450	150	1	20	100	10	25	10	-25		1500*	2	35*	138			
"	1955	東芝	PA	35	3.5	800	7.5W (T _c =25°C)	175	1mA	15	>10	5	500		P ₀ = 3.2W (f = 175MHz, V _{CE} = 13.5V, P _i = 0.15W)				<15	84B			
★ "	"	"	"	35	3.5	3.5A	35W (T _c =25°C)	175	1mA	15	50	5	1A		P ₀ = 17W (f = 175MHz, V _{CE} = 12.5V, P _i = 1.3W)					135			
"	日電	"	Si.E	75	4	1A	750	150	1	40	90	10	500	10	-150	P ₀ = 1.8W, η > 60% (V _{CE} = 12V, f = 27MHz, P _i = 35mW)	250*	14	14	225			
"	1958																						
"	1959	東芝	AF.SW	Si.E	35	5	500	500	150	0.1	35	70-240	1	100	6	-20		300*	7		138 2SA562 とコンプリ)		
"	1960	富士通	SW	Si.EP	20	4	200	300	150	0.4	15	60	1	10		t _r = 4nS, t _f = 9nS t _{sig} = 6nS				275			